TLV8x3 3-Pin Voltage Supervisors with Active-Low, Open-Drain Reset

1 Features

- 3-Pin SOT23 Package
- Supply Current: 9 μA (Typical)
- Precision Supply Voltage Monitor: 2.5 V, 3 V, 3.3 V, 5 V
- Power-On Reset Generator with Fixed Delay Time of 200 ms
- · Pin-for-Pin Compatible with MAX803
- Temperature Range: –40°C to +125°C
- Open-Drain, RESET Output

2 Applications

- · Factory Automation
- · Portable and Battery-Powered Equipment
- Set-Top Boxes
- Servers
- Appliances
- Electricity Meters
- Building Automation

3 Description

The TLV8x3 family of supervisory circuits provides circuit initialization and timing supervision, primarily for DSPs and processor-based systems.

The TLV803, TLV853, and TLV863 are functionally equivalent. The TLV853 and TLV863 provide an alternate pinout of the TLV803. The newer TLV803E device is a pin-to-pin alternative to all of these 3.

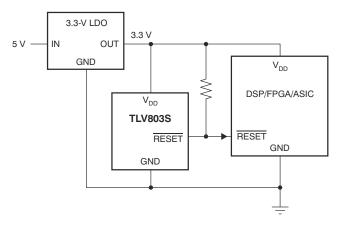
During power on, \overline{RESET} asserts when the supply voltage (V_{DD}) exceeds 1.1 V. Thereafter, the supervisory circuit monitors V_{DD} and keeps \overline{RESET} active as long as V_{DD} remains below the threshold voltage V_{IT} . An internal timer delays the return of the output to the inactive state (high) to ensure proper system reset. The delay time $(t_{d(typ)} = 200 \text{ ms})$ starts after V_{DD} exceeds the threshold voltage, V_{IT} . When the supply voltage drops below the V_{IT} threshold voltage, the output is active (low) again. All the devices in this family have a fixed sense-threshold voltage (V_{IT}) set by an internal voltage divider.

The product spectrum is designed for supply voltages of 2.5 V, 3 V, 3.3 V, and 5 V. These devices are available in a 3-pin SOT-23 package. The TLV803 devices are characterized for operation over a temperature range of –40°C to +125°C.

Device Information (1)

PART NUMBER		PACKAGE	BODY SIZE (NOM)		
	TLV8x3	SOT-23 (3)	2.92 mm × 1.30 mm		

 For all available packages, see the package option addendum at the end of the data sheet.



Typical Application

Table of Contents

2 Apr	tures		8.4 Device Functional Modes	
	olications		9 Application and Implementation	
	cription		9.1 Application Information	
	rision History		9.2 Typical Application	
	rice Comparison		10 Power Supply Recommendations	
	Configuration and Functions		11 Layout	
	Functions		11.1 Layout Guidelines	
	ecificationsAbsolute Maximum Ratings ⁽¹⁾		11.2 Layout Example 12 Device and Documentation Support	
	ESD Ratings		12.1 Device Support	
	Thermal Information		12.2 Documentation Support	
	Recommended Operating Conditions		12.3 Related Links	
	Electrical Characteristics		12.4 Support Resources	
	Switching Characteristics		12.5 Trademarks	
	Typical Characteristics		12.6 Electrostatic Discharge Caution	
	ailed Description		12.7 Glossary	
	Overview		13 Mechanical, Packaging, and Orderable	
8.2	Functional Block Diagram	8	Information	15
8.3	Feature Description	8		
NOTI	evision History E: Page numbers for previous revisions mages from Revision D (November 2020)	•	from page numbers in the current version.	Page
• C	orrected missed VDD change from 7 to 6	.5 in <i>Abso</i>	lute Maximum Ratings in note 2	5
<u> </u>	f Baddalan 0 (0 - 1 - 1 - 1 0 0 4 5	·	-law D (Navaranham 2000)	
	nges from Revision C (September 2015	-		Page
	_	-	d cross-references throughout the document	
 Ac 	dded new sentence regarding TLV803E to	o Descript	tion section	1
• CI	hanged VDD from 7 to 6.5 in <i>Absolute Ma</i>	aximum R	atings	5
• CI	hanged V _O @ 500µA from 0.2 to 0.3 in <i>E</i>	lectrical C	Characteristics	6
			aracteristics	
			tics	
• De	_		verdrive Voltage in Typical Characteristics	/
	hanged figure from Pulse Duration to V_{OL}			
• CI	0 0	, I _{OL} in the	e Typical Application Section	
	nges from Revision B (August 2011) to			
Char	nges from Revision B (August 2011) to	Revision		Page
Char	nges from Revision B (August 2011) to	Revision	C (September 2015)	Page
 Char Ac Cl 	nges from Revision B (August 2011) to dded TLV853 device to data sheet hanged device part numbers shown on pa	Revision	C (September 2015) er to show single TLV803 device instead of letter	Page1
• Ac	nges from Revision B (August 2011) to dded TLV853 device to data sheet hanged device part numbers shown on pa	Revision age heade	C (September 2015) er to show single TLV803 device instead of letter	Page1 ed1
• Ad de	nges from Revision B (August 2011) to dded TLV853 device to data sheet hanged device part numbers shown on paevice versionsdded Device Information and ESD Rating	Revision age heade	C (September 2015) er to show single TLV803 device instead of letter	Page
• Ad • Ad • Ad	nges from Revision B (August 2011) to dded TLV853 device to data sheet	Revision age heade	C (September 2015) er to show single TLV803 device instead of letter entation, Power-Supply Recommendations, Layo	Page
• Ad • Ad • Ad • Ad • Ad	nges from Revision B (August 2011) to dided TLV853 device to data sheet	Revision age heade s tables d Implement	er to show single TLV803 device instead of letterentation, Power-Supply Recommendations, Layon, Packaging, and Orderable Information sections	Page1 ed1 put, s1
• Ad	nges from Revision B (August 2011) to dided TLV853 device to data sheet	Revision age heade	C (September 2015) er to show single TLV803 device instead of letter entation, Power-Supply Recommendations, Layo I, Packaging, and Orderable Information sections	Page1 ed1 out, s1
• Ad	nges from Revision B (August 2011) to dded TLV853 device to data sheet	Revision age heade s tables d Implement dechanical	C (September 2015) er to show single TLV803 device instead of letter entation, Power-Supply Recommendations, Layo I, Packaging, and Orderable Information sections configurations and Functions section.	Page
• Ad	nges from Revision B (August 2011) to dded TLV853 device to data sheet	Revision age heade s tables d Implement dechanical	C (September 2015) er to show single TLV803 device instead of letter entation, Power-Supply Recommendations, Layo I, Packaging, and Orderable Information sections	Page
• Ad • CI • Ad • CI • CI • CI • CI • CI • CI	nges from Revision B (August 2011) to dided TLV853 device to data sheet	Revision age heade s tables d Implement dechanical d to Pin Contemperat	C (September 2015) er to show single TLV803 device instead of letter entation, Power-Supply Recommendations, Layo I, Packaging, and Orderable Information sections configurations and Functions section.	Page
• Ad • Ad • Ad • Ad • Ad • CI • Ad • CI • CI • Do • CI • Do • CI	nges from Revision B (August 2011) to ded TLV853 device to data sheet	Revision age heade stables d Implement dechanical d to Pin Co temperat	C (September 2015) er to show single TLV803 device instead of letters entation, Power-Supply Recommendations, Layo I, Packaging, and Orderable Information sections configurations and Functions section	Page1 ed1 out, s11 tement
• Ad Do Cl	nges from Revision B (August 2011) to ded TLV853 device to data sheet	Revision age heade as tables ad Implement dechanical d to Pin Contemperat ute Maximum ed therma	C (September 2015) er to show single TLV803 device instead of letters entation, Power-Supply Recommendations, Layo I, Packaging, and Orderable Information sections configurations and Functions section	Page1 ed1 out,1 tement1

• Changed temperature noted in Switching Characteristics condition statement	6
Changes from Revision A (June 2011) to Revision B (August 2011)	Page
Added new paragraph regarding TLV863 to Description section	
Added TLV863 pinout to front page	1
Added TLV863 to Thermal Information	
Added TLV863M to Negative-Going Input Threshold Voltage parameter	6
Added TLV863M to Hysteresis parameter	6
Added TLV863 to Functional Block Diagram	

5 Device Comparison

Table 5-1. Device Threshold Options

DEVICE	THRESHOLD VOLTAGE
TLV803Z	2.25 V
TLV803R	2.64 V
TLV803S	2.93 V
TLV803M	4.38 V
TLV853M	4.38 V
TLV863M	4.38 V

Table 5-2. Device Family Comparison

DEVICE	FUNCTION
TLV803	Open-Drain, RESET Output
TLV809	Push-Pull, RESET Output
TLV810	Push-Pull, RESET Output

6 Pin Configuration and Functions

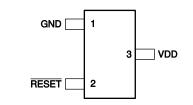


Figure 6-1. TLV803: DBZ Package 3-Pin SOT-23 Top View

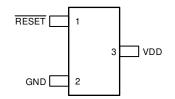


Figure 6-2. TLV853: DBZ Package 3-Pin SOT-23 Top View

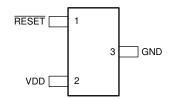


Figure 6-3. TLV863: DBZ Package 3-Pin SOT-23 Top View

Pin Functions

	PIN			I/O	DESCRIPTION		
NAME	TLV803 TLV853 TLV863		TLV863	1/0	DESCRIPTION		
GND	1	2	3	_	Ground pin.		
RESET	2	2 1 1 0		О	$\overline{\text{RESET}}$ is an open-drain output that is driven to a low impedance state when RESET is asserted. $\overline{\text{RESET}}$ remains low (asserted) for the delay time (t _d) after V _{DD} exceeds V _{IT} Use a 10-kΩ to 1-MΩ pullup resistor on this pin. The pullup voltage is not limited by V _{DD} .		
VDD	3	3	2	1	Supply voltage pin. It is good analog design practice to place a 0.1-µF ceramic capacitor close to this pin.		

7 Specifications

7.1 Absolute Maximum Ratings (1)

over operating junction temperature range (unless otherwise noted)

		MIN	MAX	UNIT
Voltage	VDD ⁽²⁾	0	6.5	V
voitage	All other pins ⁽²⁾	-0.3	+6.5	V
	Maximum low output current, I _{OL}		5	
Current	Maximum high output current, I _{OH}		– 5	mA
Current	Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{DD}$)		±20	IIIA
	Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{DD}$)		±20	
Temperature	Operating junction temperature range, T _J	-40	125	°C
remperature	Storage temperature range, T _{stg}	-65	150	

- (1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values are with respect to GND. For reliable operation the device should not be operated at 6.5 V for more than t = 1000h continuously

7.2 ESD Ratings

			VALUE	UNIT
V	Electrostatic	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	V
V _(ESD)	discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±500	\ \ \ \

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Thermal Information

		TLV8x3	
	THERMAL METRIC(1)	DBZ (SOT-23)	UNITS
		3 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	328.5	°C/W
R _{0JC(top)}	Junction-to-case (top) thermal resistance	135.4	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	58.3	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	5.2	°C/W
ΨЈВ	Junction-to-board characterization parameter	59.6	°C/W
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

7.4 Recommended Operating Conditions

at specified temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V_{DD}	Supply voltage	1.1	6	٧
TJ	Operating junction temperature	-40	125	°C

7.5 Electrical Characteristics

over recommended operating junction temperature range (unless otherwise noted)

	PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
	Low-level output voltage		V _{DD} = 2 V to 6 V, I _{OL} = 500 μA			0.3	
V _{OL}			V _{DD} = 3.3 V, I _{OL} = 2 mA			0.4	V
			V _{DD} = 6 V, I _{OL} = 4 mA			0.4	
	Power-up reset voltage ⁽¹⁾		I _{OL} = 50 μA, V _{OL} < 0.2 V	1.1			V
	Negative-going input threshold voltage ⁽²⁾	TLV803Z		2.20	2.25	2.30	
		TLV803R	T ₁ = - 40°C to +125°C	2.58	2.64	2.70	V
V_{IT-}		TLV803S	- 1j 40 C to +125 C	2.87	2.93	2.99	
		TLV8x3M		4.28	4.38	4.48	
		TLV803Z		30			
	Ultratanasia	TLV803R	T - 25°C - 50		35		
V _{hys}	Hysteresis	TLV803S	- T _J = 25°C, I _{OL} = 50 μA		40		mV
	TLV8x3M	TLV8x3M			60		
	Supply current		V _{DD} = 2 V, output unconnected		9	15	
I _{DD}			V _{DD} = 6 V, output unconnected		20	30	μA
I _{OH}	Output leakage current		V _{DD} = 6 V			350	nA

- (1) The lowest supply voltage at which $\overline{\text{RESET}}$ becomes valid. $t_{r,VDD} \le 66.7 \text{ V/ms}$.
- (2) To ensure best stability of the threshold voltage, place a bypass capacitor (0.1-µF ceramic) near the supply terminals.

7.6 Switching Characteristics

over operating temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _w	Pulse duration at V _{DD}	V _{DD} = 1.08 V _{IT} to 0.92 V _{IT}		10		μs
t _d	Delay time	V _{DD} ≥ V _{IT} + 0.2 V; see Timing Diagram	120	200	280	ms

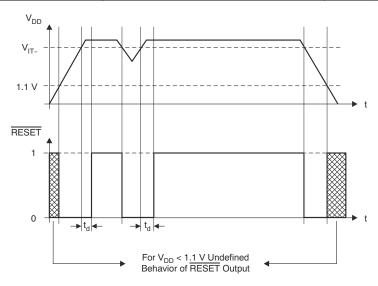


Figure 7-1. Timing Diagram

7.7 Typical Characteristics

at $T_J = 25$ °C, $V_{IT-} = 4.38$ V, and $V_{DD} = 5.0$ V (unless otherwise noted)

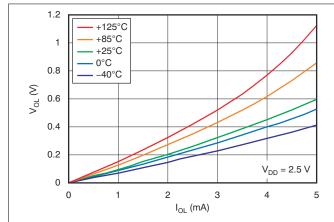


Figure 7-2. Low-Level Output Voltage vs Low-Level Output Current

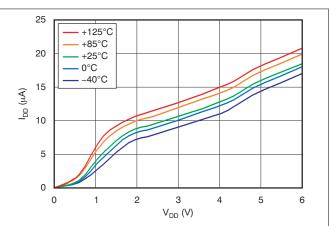


Figure 7-3. Supply Current vs Supply Voltage

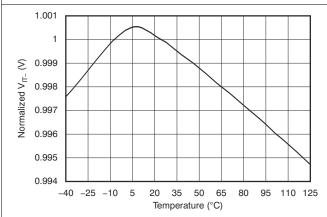


Figure 7-4. Normalized to 25°C Negative-Going Input Threshold Voltage vs Temperature

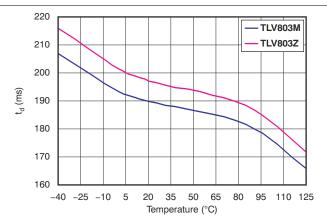


Figure 7-5. Delay Time vs Temperature

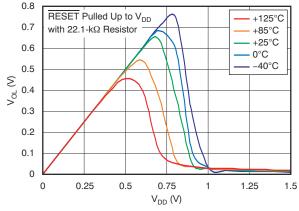


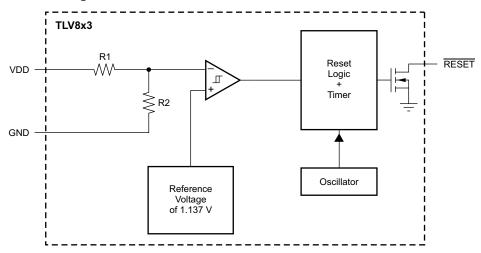
Figure 7-6. Power-Up Low-Level Output Voltage vs Supply Voltage

8 Detailed Description

8.1 Overview

The TLV803 family of supervisory circuits provides circuit initialization and timing supervision. The TLV853 and TLV863 are both functionally equivalent to the TLV803. These devices output a logic low whenever V_{DD} drops below the negative-going threshold voltage (V_{IT_-}). The output, \overline{RESET} , remains low for approximately 200 ms after the V_{DD} voltage exceeds the positive-going threshold voltage ($V_{IT_-} + V_{hys}$). These devices are designed to ignore fast transients on the V_{DD} pin.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 V_{DD} Transient Rejection

The TLV803 has built-in rejection of fast transients on the V_{DD} pin. The rejection of transients depends on both the duration and the amplitude of the transient. The amplitude of the transient is measured from the bottom of the transient to the negative threshold voltage of the TLV803, as shown in Figure 8-1.

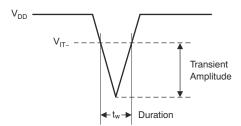


Figure 8-1. Voltage Transient Measurement

The TLV803 does not respond to transients that are fast duration/low amplitude or long duration/small amplitude. Transients meeting or longer than the t_w specified in the switching characteristics section triggers a reset.

8.3.2 Reset During Power Up and Power Down

The TLV803 output is valid when V_{DD} is greater than 1.1 V. When V_{DD} is less than 1.1 V, the output transistor turns off and becomes high impedance. The voltage on the \overline{RESET} pin rises to the voltage level connected to the pull-up resistor. Figure 8-2 shows a typical waveform for power-up, assuming the \overline{RESET} pin has a pull-up resistor connected to the V_{DD} pin.

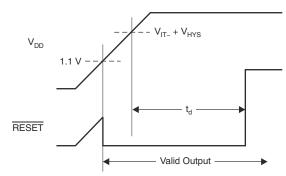


Figure 8-2. Power-Up Response

8.3.3 Bidirectional Reset Pins

Some microcontrollers have bidirectional reset pins that act as both inputs and outputs. In a situation where the TLV803 is pulling the RESET line low while the microcontroller is trying the force the RESET line high, a series resistor should be placed between the output of the TLV803 and the RESET pin of the microcontroller to protect against excessive current flow. Figure 8-3 shows the connection of the TLV803 to a microcontroller using a series resistor to drive a bidirectional RESET line.

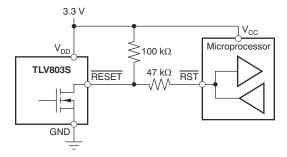


Figure 8-3. Connection To Bidirectional Reset Pin

8.4 Device Functional Modes

8.4.1 Normal Operation (VDD > Power-Up Reset Voltage)

When the voltage on VDD is greater than 1.1 V, the \overline{RESET} signal asserts when V_{DD} is less than V_{IT-} and deasserts when V_{DD} is greater than V_{IT-} .

8.4.2 Power On Reset (VDD < Power-Up Reset Voltage)

When the voltage on VDD is lower than the required voltage to internally pull the asserted output to GND (power-up reset voltage), both outputs are in a high-impedance state.

9 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

9.1.1 Monitoring Multiple Supplies

Because the TLV803 has an open-drain output, multiple TLV803 outputs can be directly tied together to form a logical OR-ing function for the RESET line. Only one pull-up resistor is required for this configuration. Figure 9-1 shows two TLV803s connected together to provide monitoring of a 3.3-V power rail and a 5.0-V power rail. A reset is generated if either power rail falls below the threshold voltage of its corresponding TLV803.

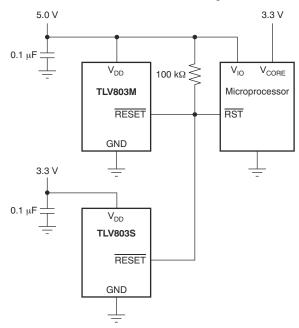


Figure 9-1. Multiple Voltage Rail Monitoring

9.1.2 Output Level Shifting

The $\overline{\text{RESET}}$ output of the TLV803 can be pulled to a maximum voltage of 6 V and can be pulled higher in voltage than V_{DD} . It is useful to provide level shifting of the output for cases where the monitored voltage is less than the useful logic levels of the load. Figure 9-2 shows the TLV803Z used to monitor a 2.5-V power rail, with a logic $\overline{\text{RESET}}$ input to a microprocessor that is connected to 5.0 V and has 5.0-V logic levels.

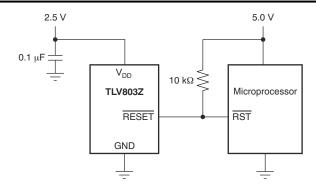


Figure 9-2. Output Voltage Level Shifting

9.2 Typical Application

Figure 9-3 shows TLV803S being used to monitor the supply rail for a DSP, FPGA, or ASIC.

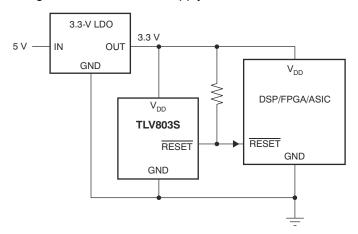


Figure 9-3. Typical Application

9.2.1 Design Requirements

This design calls for a 3.3-V rail to be monitored. The design resets if the supply rail falls below 2.93 V. The output must satisfy 3.3-V CMOS logic.

9.2.2 Detailed Design Procedure

Select the TLV803S to satisfy the voltage threshold requirement.

Place a pullup resistor on RESET to VDD in order to satisfy the output logic requirement.

9.2.3 Application Curves

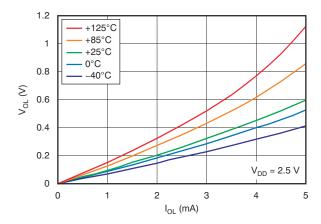


Figure 9-4. Low-Level Output Voltage vs Low-Level Output Current

10 Power Supply Recommendations

These devices are designed to operate from an input voltage supply range between 1.1 V and 6 V.

11 Layout

11.1 Layout Guidelines

Place the $C_{\mbox{\scriptsize IN}}$ decoupling capacitor close to the device.

11.2 Layout Example

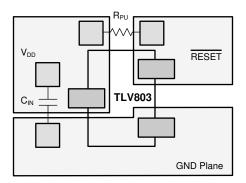


Figure 11-1. Layout Example (DBZ Package)

12 Device and Documentation Support

12.1 Device Support

12.1.1 Development Support

12.1.1.1 Evaluation Modules

An evaluation module (EVM) is available to assist in the initial circuit performance evaluation using the TLV803. The TLV803SEVM-019 evaluation module (and related user guide) can be requested at the Texas Instruments website through the product folders or purchased directly from the TI eStore.

12.1.1.2 Spice Models

Computer simulation of circuit performance using SPICE is often useful when analyzing the performance of analog circuits and systems. SPICE models for the TLV803, TLV853, and TLV863 are available through the respective device product folders under *Tools & Software*.

12.2 Documentation Support

12.2.1 Related Documentation

TLV803SEVM-019 User's Guide. Literature number SLVU461.

12.3 Related Links

Table 12-1 lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

	Tubic 12 1. Indiated Elling												
PARTS	PRODUCT FOLDER	SAMPLE & BUY	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY								
TLV803	Click here	Click here	Click here	Click here	Click here								
TLV853	Click here	Click here	Click here	Click here	Click here								
TLV863	Click here	Click here	Click here	Click here	Click here								

Table 12-1. Related Links

12.4 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

12.5 Trademarks

TI E2E[™] is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

12.6 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.7 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
TLV803MDBZR	ACTIVE	SOT-23	DBZ	3	3000	RoHS & Green	NIPDAUAG SN	Level-1-260C-UNLIM	-40 to 125	VOUQ	Samples
TLV803MDBZT	ACTIVE	SOT-23	DBZ	3	250	RoHS & Green	NIPDAUAG SN	Level-1-260C-UNLIM	-40 to 125	VOUQ	Samples
TLV803RDBZR	ACTIVE	SOT-23	DBZ	3	3000	RoHS & Green	NIPDAU SN NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	VOSQ	Samples
TLV803RDBZT	ACTIVE	SOT-23	DBZ	3	250	RoHS & Green	NIPDAUAG SN	Level-1-260C-UNLIM	-40 to 125	VOSQ	Samples
TLV803SDBZR	ACTIVE	SOT-23	DBZ	3	3000	RoHS & Green	NIPDAU SN NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	VOTQ	Samples
TLV803SDBZT	ACTIVE	SOT-23	DBZ	3	250	RoHS & Green	NIPDAUAG SN	Level-1-260C-UNLIM	-40 to 125	VOTQ	Samples
TLV803ZDBZR	ACTIVE	SOT-23	DBZ	3	3000	RoHS & Green	NIPDAU SN NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	VORQ	Samples
TLV803ZDBZT	ACTIVE	SOT-23	DBZ	3	250	RoHS & Green	NIPDAUAG SN	Level-1-260C-UNLIM	-40 to 125	VORQ	Samples
TLV853MDBZR	ACTIVE	SOT-23	DBZ	3	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	ZGM4	Samples
TLV853MDBZT	ACTIVE	SOT-23	DBZ	3	250	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	ZGM4	Samples
TLV863MDBZR	ACTIVE	SOT-23	DBZ	3	3000	RoHS & Green	NIPDAUAG SN	Level-1-260C-UNLIM	-40 to 125	VTWM	Samples
TLV863MDBZT	ACTIVE	SOT-23	DBZ	3	250	RoHS & Green	NIPDAUAG SN	Level-1-260C-UNLIM	-40 to 125	VTWM	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

PACKAGE OPTION ADDENDUM

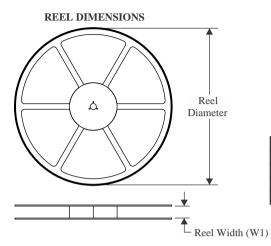
2-Aug-2022

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

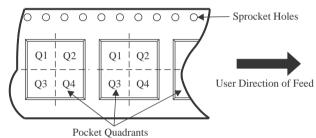
TAPE AND REEL INFORMATION



TAPE DIMENSIONS KO P1 BO BO Cavity AO

A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



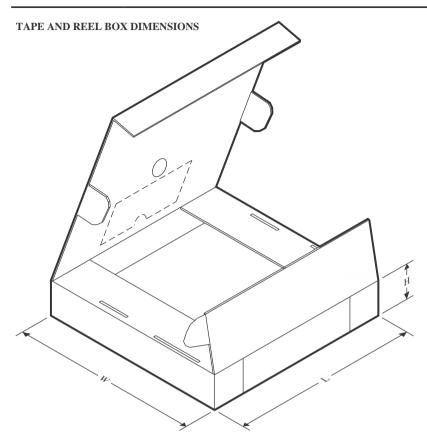
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter	Reel Width	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TI \ (000MDDZD	207.00	557		2222	(mm)	W1 (mm)		0.05	4.00	4.0		
TLV803MDBZR	SOT-23	DBZ	3	3000	179.0	8.4	3.15	2.95	1.22	4.0	8.0	Q3
TLV803MDBZR	SOT-23	DBZ	3	3000	178.0	9.0	3.15	2.77	1.22	4.0	8.0	Q3
TLV803MDBZT	SOT-23	DBZ	3	250	179.0	8.4	3.15	2.95	1.22	4.0	8.0	Q3
TLV803RDBZR	SOT-23	DBZ	3	3000	180.0	8.4	2.9	3.35	1.35	4.0	8.0	Q3
TLV803RDBZR	SOT-23	DBZ	3	3000	178.0	9.0	3.15	2.77	1.22	4.0	8.0	Q3
TLV803RDBZT	SOT-23	DBZ	3	250	179.0	8.4	3.15	2.95	1.22	4.0	8.0	Q3
TLV803RDBZT	SOT-23	DBZ	3	250	178.0	9.0	3.15	2.77	1.22	4.0	8.0	Q3
TLV803SDBZR	SOT-23	DBZ	3	3000	178.0	9.0	3.15	2.77	1.22	4.0	8.0	Q3
TLV803SDBZR	SOT-23	DBZ	3	3000	179.0	8.4	3.15	2.95	1.22	4.0	8.0	Q3
TLV803SDBZR	SOT-23	DBZ	3	3000	180.0	8.4	2.9	3.35	1.35	4.0	8.0	Q3
TLV803SDBZT	SOT-23	DBZ	3	250	178.0	9.0	3.15	2.77	1.22	4.0	8.0	Q3
TLV803SDBZT	SOT-23	DBZ	3	250	179.0	8.4	3.15	2.95	1.22	4.0	8.0	Q3
TLV803ZDBZR	SOT-23	DBZ	3	3000	178.0	9.0	3.15	2.77	1.22	4.0	8.0	Q3
TLV803ZDBZR	SOT-23	DBZ	3	3000	180.0	8.4	2.9	3.35	1.35	4.0	8.0	Q3
TLV803ZDBZR	SOT-23	DBZ	3	3000	179.0	8.4	3.15	2.95	1.22	4.0	8.0	Q3
TLV803ZDBZT	SOT-23	DBZ	3	250	179.0	8.4	3.15	2.95	1.22	4.0	8.0	Q3

PACKAGE MATERIALS INFORMATION

3-Jun-2022

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV853MDBZR	SOT-23	DBZ	3	3000	179.0	8.4	3.15	2.95	1.22	4.0	8.0	Q3
TLV853MDBZR	SOT-23	DBZ	3	3000	178.0	9.0	3.15	2.77	1.22	4.0	8.0	Q3
TLV853MDBZT	SOT-23	DBZ	3	250	179.0	8.4	3.15	2.95	1.22	4.0	8.0	Q3
TLV863MDBZR	SOT-23	DBZ	3	3000	178.0	9.0	3.15	2.77	1.22	4.0	8.0	Q3
TLV863MDBZR	SOT-23	DBZ	3	3000	179.0	8.4	3.15	2.95	1.22	4.0	8.0	Q3
TLV863MDBZT	SOT-23	DBZ	3	250	179.0	8.4	3.15	2.95	1.22	4.0	8.0	Q3



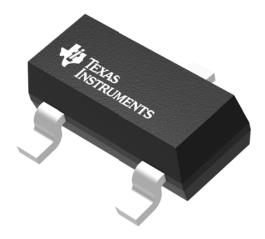
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV803MDBZR	SOT-23	DBZ	3	3000	200.0	183.0	25.0
TLV803MDBZR	SOT-23	DBZ	3	3000	180.0	180.0	18.0
TLV803MDBZT	SOT-23	DBZ	3	250	200.0	183.0	25.0
TLV803RDBZR	SOT-23	DBZ	3	3000	210.0	185.0	35.0
TLV803RDBZR	SOT-23	DBZ	3	3000	180.0	180.0	18.0
TLV803RDBZT	SOT-23	DBZ	3	250	200.0	183.0	25.0
TLV803RDBZT	SOT-23	DBZ	3	250	180.0	180.0	18.0
TLV803SDBZR	SOT-23	DBZ	3	3000	180.0	180.0	18.0
TLV803SDBZR	SOT-23	DBZ	3	3000	200.0	183.0	25.0
TLV803SDBZR	SOT-23	DBZ	3	3000	210.0	185.0	35.0
TLV803SDBZT	SOT-23	DBZ	3	250	180.0	180.0	18.0
TLV803SDBZT	SOT-23	DBZ	3	250	200.0	183.0	25.0
TLV803ZDBZR	SOT-23	DBZ	3	3000	180.0	180.0	18.0
TLV803ZDBZR	SOT-23	DBZ	3	3000	210.0	185.0	35.0
TLV803ZDBZR	SOT-23	DBZ	3	3000	200.0	183.0	25.0
TLV803ZDBZT	SOT-23	DBZ	3	250	203.0	203.0	35.0
TLV853MDBZR	SOT-23	DBZ	3	3000	200.0	183.0	25.0
TLV853MDBZR	SOT-23	DBZ	3	3000	180.0	180.0	18.0

PACKAGE MATERIALS INFORMATION

3-Jun-2022

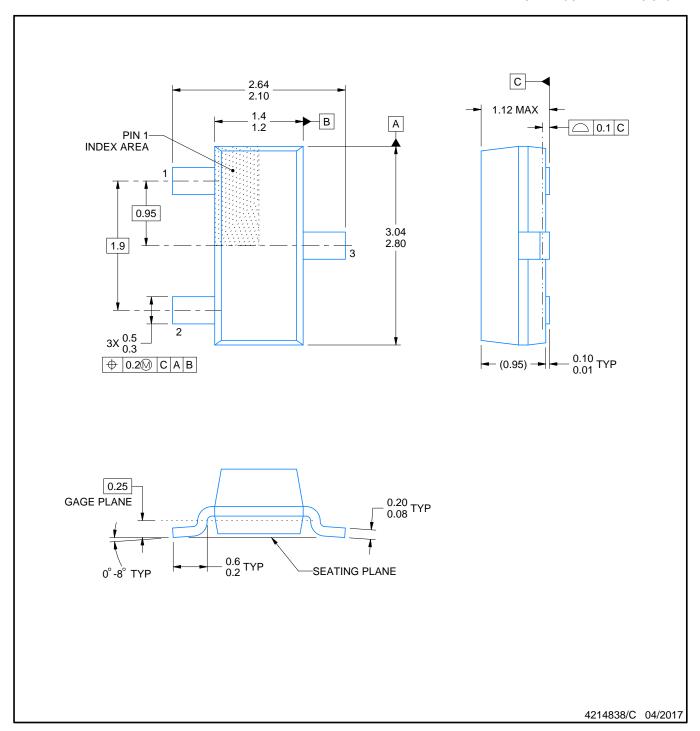
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV853MDBZT	SOT-23	DBZ	3	250	200.0	183.0	25.0
TLV863MDBZR	SOT-23	DBZ	3	3000	180.0	180.0	18.0
TLV863MDBZR	SOT-23	DBZ	3	3000	200.0	183.0	25.0
TLV863MDBZT	SOT-23	DBZ	3	250	200.0	183.0	25.0



Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.



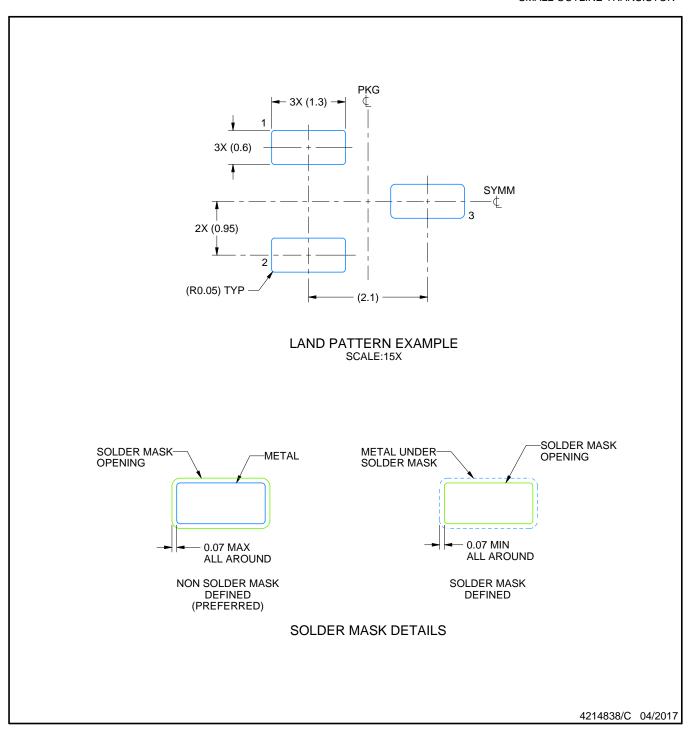
SMALL OUTLINE TRANSISTOR



NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 This drawing is subject to change without notice.
 Reference JEDEC registration TO-236, except minimum foot length.

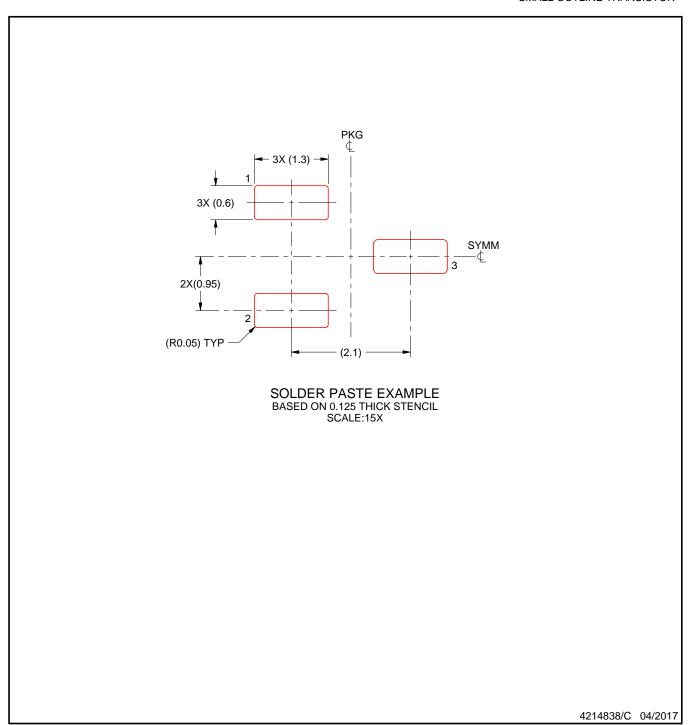
SMALL OUTLINE TRANSISTOR



NOTES: (continued)

4. Publication IPC-7351 may have alternate designs.5. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

^{6.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

^{7.} Board assembly site may have different recommendations for stencil design.